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#### NCE N-Channel Enhancement Mode Power MOSFET

#### **General Features**

•  $V_{DS} = 50V, I_D = 0.22A$ 

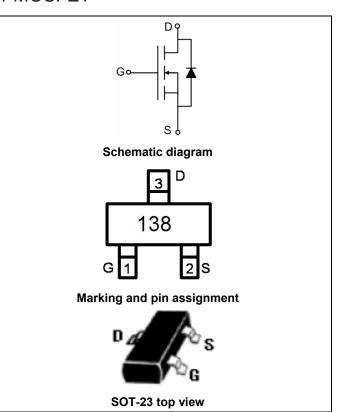
 $R_{DS(ON)} < 3\Omega$  @  $V_{GS}=5V$ 

 $R_{DS(ON)}$  <  $2\Omega$  @  $V_{GS}$ =10V

- Lead free product is acquired
- Surface mount package

#### **Application**

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays



### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
138	BSS138	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	50	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Drain Current-Continuous	I <sub>D</sub>	0.22	Α	
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	0.88	Α	
Maximum Power Dissipation	P <sub>D</sub>	0.35	W	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C	

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)   R <sub>BJA</sub>   350   C/W		$R_{ heta JA}$	350	°C/W
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### **Electrical Characteristics (T<sub>A</sub>=25**°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	50	65	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V	-	-	0.5	μΑ



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# **BSS138**

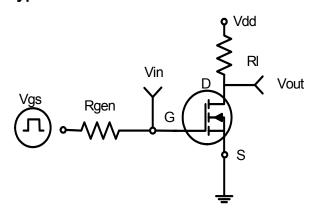
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	0.8	1.2	1.6	V
Drain-Source On-State Resistance	D	V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A	-	1.2	3	Ω
Diain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A	-	1	2	Ω
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =0.2A	0.12	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,	-	27	-	PF
Output Capacitance	Coss	V <sub>DS</sub> -23V, V <sub>GS</sub> -0V, F=1.0MHz	-	12	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F = 1.01VII 12	-	6	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	2.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =0.22A	-	6	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =6 $\Omega$	-	20	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Qg	$V_{DS}$ =25V, $I_{D}$ =0.3A, $V_{GS}$ =10V	-	1.7	2.4	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =0.22A	-	-	1.3	V
Diode Forward Current (Note 2)	Is	-	-	-	0.22	Α

#### Notes:

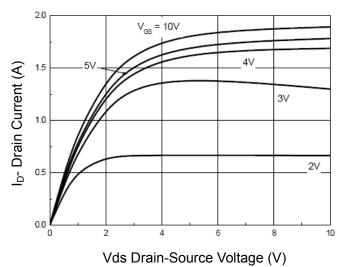
- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



### **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Output Characteristics** 

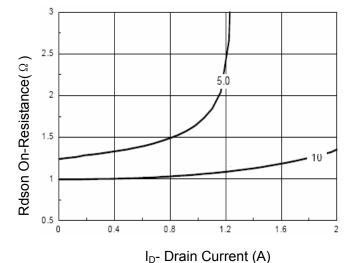


Figure 5 Drain-Source On-Resistance

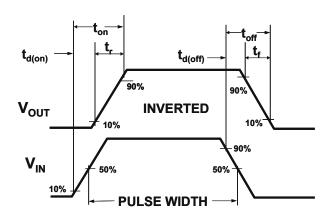


Figure 2:Switching Waveforms

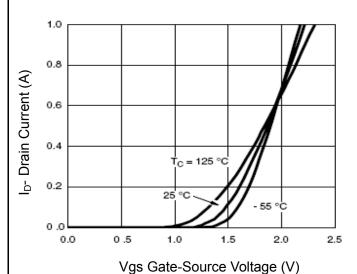
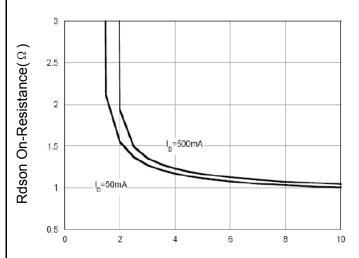
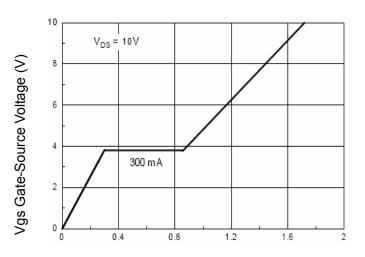


Figure 4 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 6 Rdson vs Vgs





Qg Gate Charge (nC) Figure 7 Gate Charge

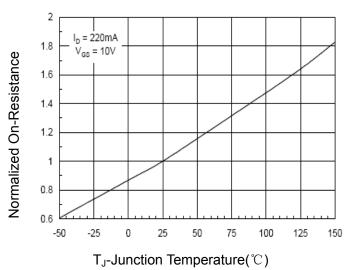


Figure 9 Drain-Source On-Resistance

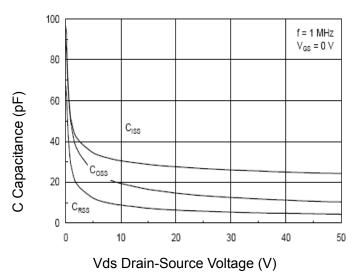
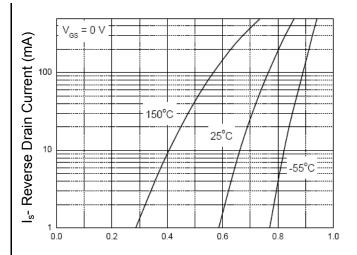
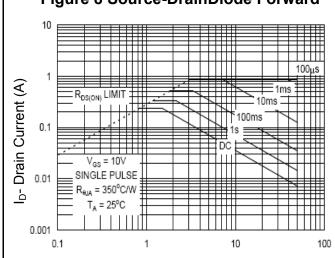


Figure 11 Capacitance vs Vds



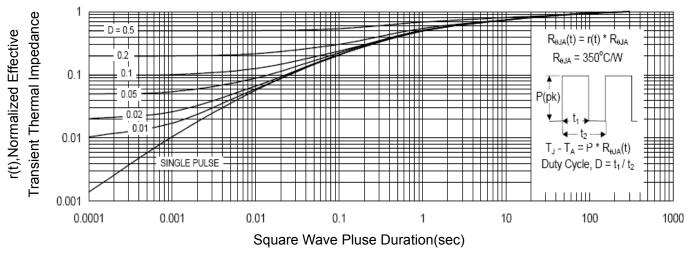
Vds Source-Drain Voltage (V)
Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V)

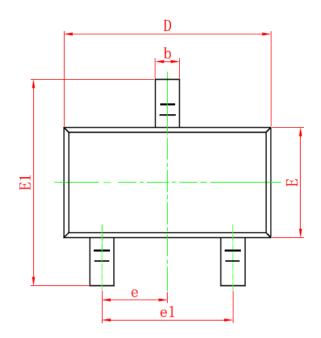
Figure 10 Safe Operation Area

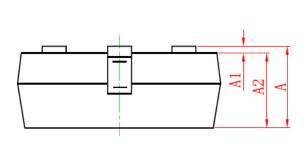


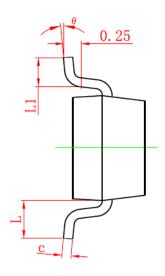


**Figure 12 Normalized Maximum Transient Thermal Impedance** 

# **SOT-23 Package Information**







Symbol	Dimensions in Millimeters			
Symbol	MIN.	MAX.		
Α	0.900	1.150		
<b>A</b> 1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		

#### **Notes**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

# **BSS138**

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